

Nagaboopathy Mohan

List of Publications by Year in descending order

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12
papers

199
citations

1307594

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1372567

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docs citations

12
times ranked

320
citing authors

#	ARTICLE	IF	CITATIONS
1	Positive Threshold Voltage Shift in AlGa _x N _{1-x} /Ga _x N HEMTs and E-Mode Operation By $\text{Al}_{1-x}\text{Ti}_x\text{O}$ Based Gate Stack Engineering. IEEE Transactions on Electron Devices, 2019, 66, 2544-2550.	3.0	36
2	Vertical Current Transport in AlGa _x N _{1-x} /Ga _x N HEMTs on Silicon: Experimental Investigation and Analytical Model. IEEE Transactions on Electron Devices, 2019, 66, 613-618.	3.0	16
3	Microwave irradiation-assisted deposition of Ga ₂ O ₃ on III-nitrides for deep-UV opto-electronics. Applied Physics Letters, 2018, 112, .	3.3	48
4	The role of surface roughness on dislocation bending and stress evolution in low mobility AlGa _x N films during growth. Journal of Applied Physics, 2018, 123, 165108.	2.5	13
5	Dislocation bending and stress evolution in Mg-doped GaN films on Si substrates. Journal of Applied Physics, 2018, 124, .	2.5	7
6	Wafer-scale epitaxial germanium (100), (111), (110) films on silicon using liquid phase crystallization. AIP Advances, 2018, 8, .	1.3	7
7	Gallium nitride transistor on glass using epoxy mediated substrate transfer technology. , 2017, , .		1
8	On the ESD behavior of AlGa _x N _{1-x} /Ga _x N schottky diodes and trap assisted failure mechanism. , 2017, , .		11
9	Curvature Management in Buffer Layer for Device Quality GaN Growth on Si (111). IETE Technical Review (Institution of Electronics and Telecommunication Engineers, India), 2016, 33, 82-87.	3.2	6
10	Integrating AlGa _x N _{1-x} /Ga _x N high electron mobility transistor with Si: A comparative study of integration schemes. Journal of Applied Physics, 2015, 118, .	2.5	16
11	Self-assembled gold nanofilms as a simple, recoverable and recyclable catalyst for nitro-reduction. Journal of Materials Chemistry A, 2015, 3, 21167-21177.	10.3	13
12	An early <i>in-situ</i> stress signature of the AlN-Si pre-growth interface for successful integration of nitrides with (111) Si. Applied Physics Letters, 2013, 103, .	3.3	25